

Docket No.: 57810-031

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of

Tatsuya KUNISATO, et al.

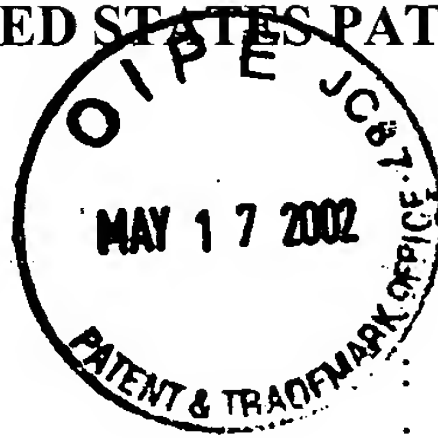
Serial No.: 10/081,842

Group Art Unit: 2815

Filed: February 25, 2002

Examiner:

For: NITRIDE-BASED SEMICONDUCTOR ELEMENT AND METHOD OF FORMING  
NITRIDE-BASED SEMICONDUCTOR



**RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS**

Commissioner for Patents  
Washington, DC 20231

Sir:

We are in receipt of the Notice to File Corrected Application Papers mailed March 19, 2002.

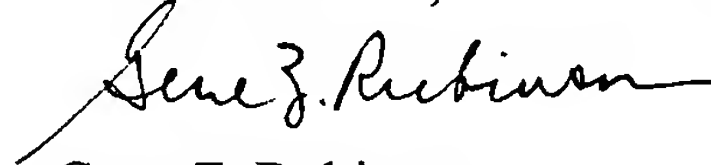
In response to this Notice, submitted herewith is an Abstract not exceeding 150 words (37 CFR 1.72 (b)). If anything further is needed, please contact the undersigned immediately.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Gene Z. Robinson  
Registration No. 33,351

600 13<sup>th</sup> Street, N.W.  
Washington, DC 20005-3096  
(202)756-8000 GZR:mlw  
Facsimile: (202)756-8087  
**Date: May 17, 2002**